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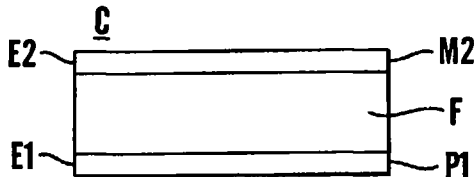
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ACTION

(54) Title: A FERROELECTRIC MEMORY CIRCUIT AND METHOD FOR ITS FABRICATION

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film contacting the conducting polymer (P₁; P₂), whereby said at least one of the electrodes (E₁; E₂) either comprises a conducting polymer contact layer (P₁; P₂) only, or a combination of a conducting polymer contact layer (P₁; P₂) and a metal film layer (M₁; M₂). A method in the fabrication of a ferroelectric memory circuit of this kind comprises steps for depositing a first contact layer of conducting polymer thin film on the substrate, depositing subsequently a ferroelectric polymer thin film on the first contact layer, and then depositing a second contact layer on the top of the ferroelectric polymer thin film.

(57) Abstract: A ferroelectric memory circuit (C) comprises a ferroelectric memory cell in the form of a ferroelectric polymer thin film (F) and first and second electrodes (E₁; E₂) respectively, contacting the ferroelectric memory cell (F) at opposite surfaces thereof, whereby a polarization state of the cell can be set, switched or detected by applying appropriate voltages to the electrodes (E₁; E₂). At least one of the electrodes (E₁; E₂) comprises at least one contact layer (P₁; P₂), said at least one contact layer (P₁; P₂) comprising a conducting polymer contacting the memory cell (C), and optionally a second layer (M₁; M₂) of a metal